

# MA3X721D, MA3X721E

## Silicon epitaxial planar type

For super-high speed switching circuit

For small current rectification

### ■ Features

- Two MA3X721s are contained in one package
- Allowing to rectify under ( $I_{F(AV)} = 200$  mA) condition (for the single diode)

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	$V_R$	30	V
Repetitive peak reverse voltage	$V_{RRM}$	30	V
Peak forward current	Single	$I_{FM}$	300
	Double*1		220
Average forward current	Single	$I_{F(AV)}$	200
	Double*1		130
Non-repetitive peak forward surge current*2	Single	$I_{FSM}$	1
	Double*1		0.7
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

Note) \*1 : Value per chip

\*2 : The peak-to-peak value in one cycle of 50 Hz sine-wave (non-repetitive)

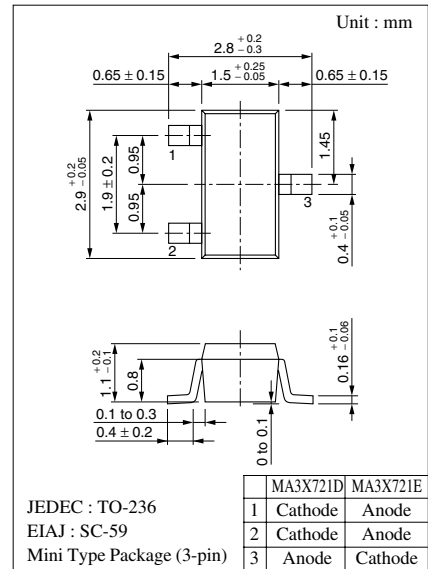
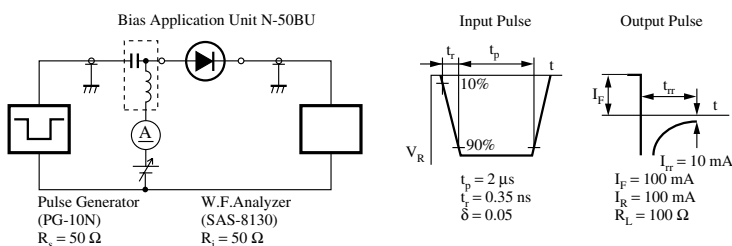
### ■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	$I_R$	$V_R = 30$ V			50	$\mu\text{A}$
Forward voltage (DC)	$V_F$	$I_F = 200$ mA			0.55	V
Terminal capacitance	$C_t$	$V_R = 10$ V, $f = 1$ MHz		30		pF
Reverse recovery time*	$t_{rr}$	$I_F = I_R = 100$ mA $I_R = 10$ mA, $R_L = 100$ $\Omega$		3		ns

Note) 1. Schottky barrier diode is sensitive to electric shock (static electricity, etc.). Due attention must be paid on the charge of a human body and the leakage of current from the operating equipment

2. Rated input/output frequency: 1 000 MHz

3. \* :  $t_{rr}$  measuring instrument



### Marking Symbol

- MA3X721D : M3H
- MA3X721E : M3F

### Internal Connection

